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# PS9305L

R08DS0013EJ0100

Rev.1.00

May 16, 2011

2.5 A OUTPUT CURRENT, HIGH CMR, IGBT GATE DRIVE, 8-PIN SDIP PHOTOCOUPLER

## DESCRIPTION

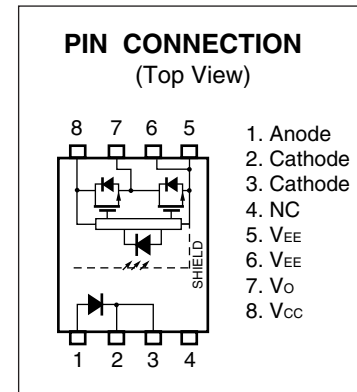
The PS9305L is an optically coupled isolator containing a GaAlAs LED on the input side and a photo diode, a signal processing circuit and a power output transistor on the output side on one chip.

The PS9305L is designed specifically for high common mode transient immunity (CMR), high output current and high switching speed.

The PS9305L is suitable for driving IGBTs and MOS FETs.

## FEATURES

- Long creepage distance (8 mm MIN.)
- Large peak output current (2.5 A MAX., 2.0 A MIN.)
- High speed switching ( $t_{PLH}$ ,  $t_{PHL}$  = 0.25  $\mu$ s MAX.)
- UVLO (Under Voltage Lock Out) protection with hysteresis
- High common mode transient immunity ( $CM_H$ ,  $CM_L$  =  $\pm 25$  kV/ $\mu$ s MIN.)
- <R> • Embossed tape product: PS9305L-E3: 2 000 pcs/reel
- <R> • Pb-Free product
- <R> • Safety standards
  - UL approved: No. E72422
  - CSA approved: No. CA 101391 (CA5A, CAN/CSA-C22.2 60065, 60950)
  - DIN EN60747-5-2 (VDE0884 Part2) approved: No. 40024069 (Option)



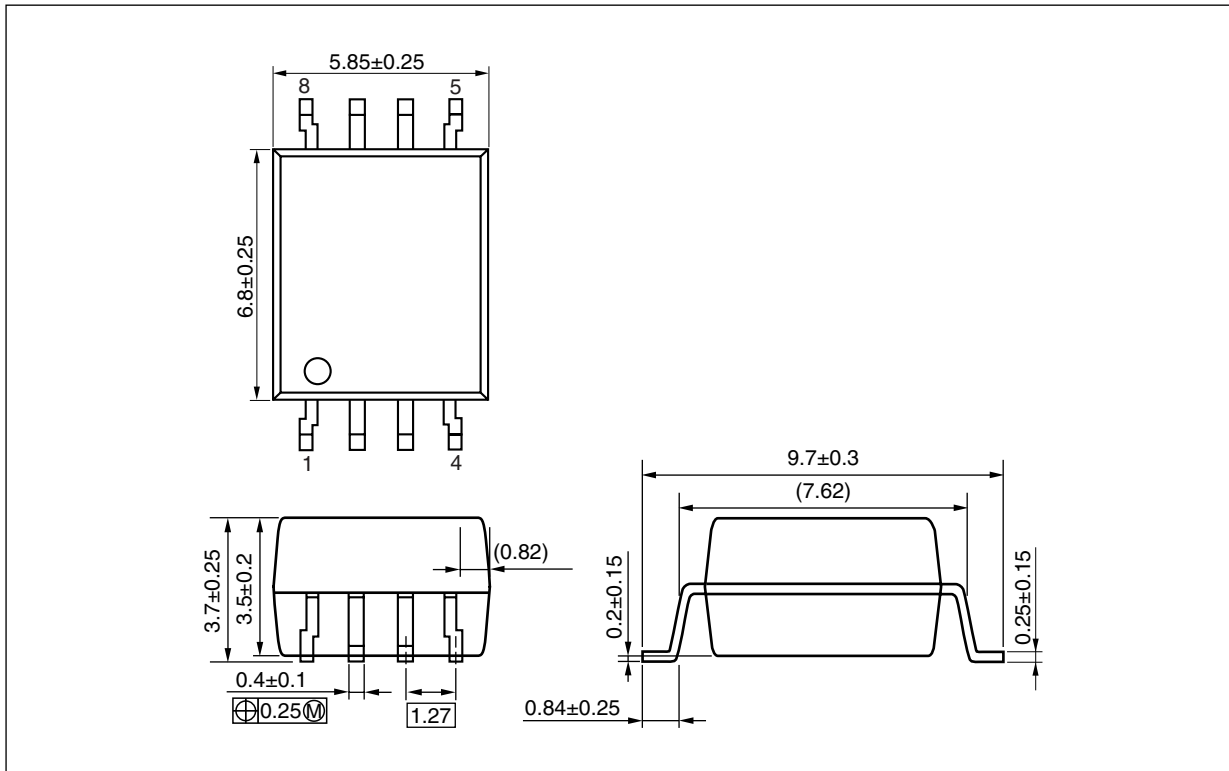
## APPLICATIONS

- IGBT, Power MOS FET Gate Driver
- Industrial inverter
- IH (Induction Heating)

The mark <R> shows major revised points.

The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.

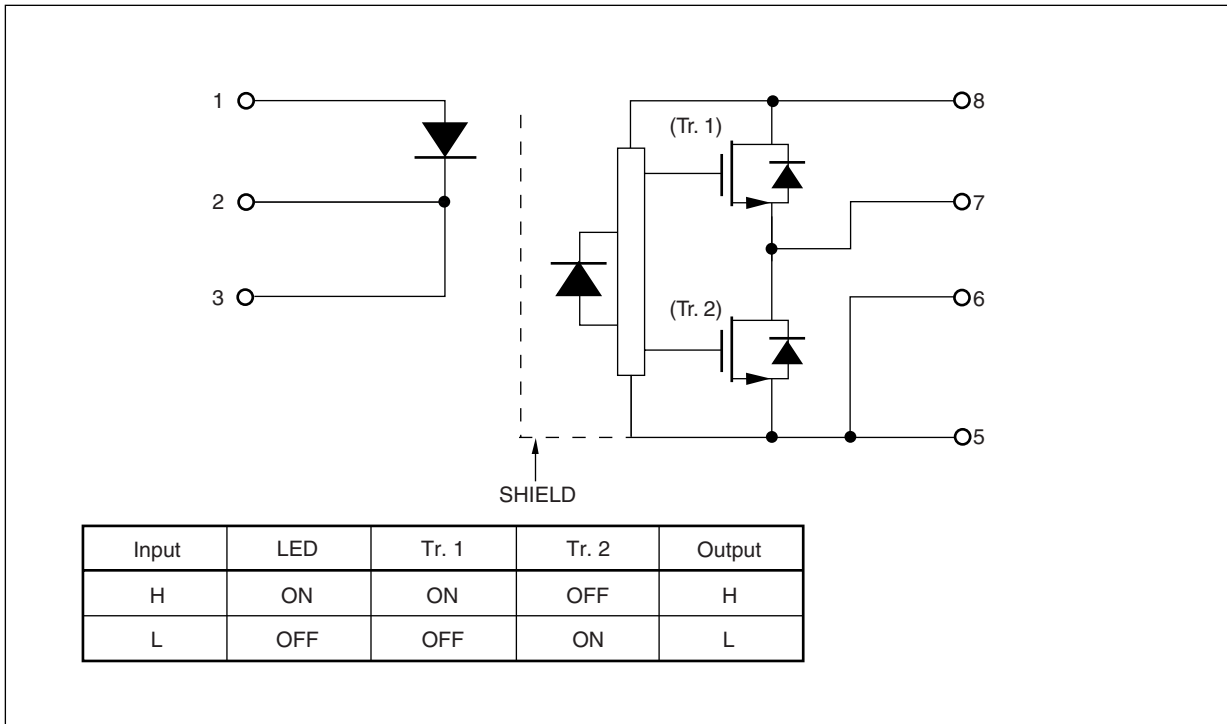
PACKAGE DIMENSIONS (UNIT: mm)



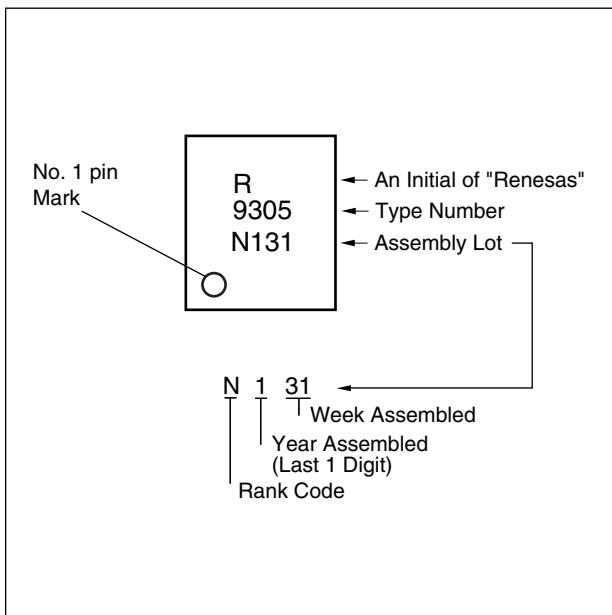
PHOTOCOUPLER CONSTRUCTION

Parameter	Unit (MIN.)
Air Distance	7 mm
Outer Creepage Distance	8 mm
Isolation Distance	0.4 mm

FUNCTIONAL DIAGRAM



<R> MARKING EXAMPLE



## &lt;R&gt; ORDERING INFORMATION

Part Number	Order Number	Solder Plating Specification	Packing Style	Safety Standard Approval	Application Part Number* <sup>1</sup>
PS9305L	PS9305L-AX	Pb-Free (Ni/Pd/Au)	20 pcs (Tape 20 pcs cut)	Standard products (UL, CSA approved)	PS9305L
PS9305L-E3	PS9305L-E3-AX		Embossed Tape 2 000 pcs/reel		
PS9305L-V	PS9305L-V-AX		20 pcs (Tape 20 pcs cut)	DIN EN60747-5-2 (VDE0884 Part2) Approved (Option)	
PS9305L-V-E3	PS9305L-V-E3-AX		Embossed Tape 2 000 pcs/reel		

\*1 For the application of the Safety Standard, following part number should be used.

ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C, unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Diode	Forward Current	I <sub>F</sub>	25	mA
	Peak Transient Forward Current (Pulse Width < 1 μs)	I <sub>F (TRAN)</sub>	1.0	A
	Reverse Voltage	V <sub>R</sub>	5	V
	Power Dissipation <sup>*1</sup>	P <sub>D</sub>	45	mW
Detector	High Level Peak Output Current <sup>*2</sup>	I <sub>OH (PEAK)</sub>	2.5	A
	Low Level Peak Output Current <sup>*2</sup>	I <sub>OL (PEAK)</sub>	2.5	A
	Supply Voltage	(V <sub>CC</sub> - V <sub>EE</sub> )	0 to 35	V
	Output Voltage	V <sub>O</sub>	0 to V <sub>CC</sub>	V
	Power Dissipation <sup>*3</sup>	P <sub>C</sub>	250	mW
Isolation Voltage <sup>*4</sup>		BV	5 000	Vr.m.s.
Operating Frequency <sup>*5</sup>		f	50	kHz
Operating Ambient Temperature		T <sub>A</sub>	-40 to +110	°C
Storage Temperature		T <sub>stg</sub>	-55 to +125	°C

<R> \*1 Reduced to 0.88 mW/°C at T<sub>A</sub> = 85°C or more.

\*2 Maximum pulse width = 10 μs, Maximum duty cycle = 0.2%

<R> \*3 Reduced to 7.36 mW/°C at T<sub>A</sub> = 85°C or more.

\*4 AC voltage for 1 minute at T<sub>A</sub> = 25°C, RH = 60% between input and output.

Pins 1-4 shorted together, 5-8 shorted together.

\*5 I<sub>OH (PEAK)</sub> ≤ 2.0 A (≤ 0.3 μs), I<sub>OL (PEAK)</sub> ≤ 2.0 A (≤ 0.3 μs)

## RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	(V <sub>CC</sub> - V <sub>EE</sub> )	15		30	V
Forward Current (ON)	I <sub>F (ON)</sub>	7	10	16	mA
Forward Voltage (OFF)	V <sub>F (OFF)</sub>	-2		0.8	V
Operating Ambient Temperature	T <sub>A</sub>	-40		110	°C

## ELECTRICAL CHARACTERISTICS

(V<sub>EE</sub> = GND, unless otherwise specified and refer to RECOMMENDED OPERATING CONDITIONS)<R>  
<R>

	Parameter	Symbol	Conditions	MIN.	TYP. <sup>*1</sup>	MAX.	Unit
Diode	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA, T <sub>A</sub> = 25°C	1.2	1.56	1.8	V
	Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 3 V, T <sub>A</sub> = 25°C			10	μA
	Terminal Capacitance	C <sub>t</sub>	f = 1 MHz, V <sub>F</sub> = 0 V, T <sub>A</sub> = 25°C		30		pF
Detector	High Level Output Current	I <sub>OH</sub>	V <sub>O</sub> = (V <sub>CC</sub> - 4 V) <sup>*2</sup>	0.5	2.0		A
			V <sub>O</sub> = (V <sub>CC</sub> - 15 V) <sup>*3</sup>	2.0			
	Low Level Output Current	I <sub>OL</sub>	V <sub>O</sub> = (V <sub>EE</sub> + 2.5 V) <sup>*2</sup>	0.5	2.0		A
			V <sub>O</sub> = (V <sub>EE</sub> + 15 V) <sup>*3</sup>	2.0			
	High Level Output Voltage	V <sub>OH</sub>	I <sub>O</sub> = -100 mA <sup>*4</sup>	V <sub>CC</sub> - 3.0	V <sub>CC</sub> - 1.5		V
	Low Level Output Voltage	V <sub>OL</sub>	I <sub>O</sub> = 100 mA		0.1	0.5	V
	High Level Supply Current	I <sub>CCH</sub>	V <sub>O</sub> = open, I <sub>F</sub> = 10 mA		1.4	3.0	mA
	Low Level Supply Current	I <sub>CCL</sub>	V <sub>O</sub> = open, V <sub>F</sub> = 0 to +0.8 V		1.3	3.0	mA
	UVLO Threshold	V <sub>UVLO+</sub>	V <sub>O</sub> > 5 V, I <sub>F</sub> = 10 mA	10.8	12.3	13.4	V
		V <sub>UVLO-</sub>		9.5	11.0	12.5	
UVLO Hysteresis	UVLO <sub>HYS</sub>	V <sub>O</sub> > 5 V, I <sub>F</sub> = 10 mA	0.4	1.3		V	
Coupled	Threshold Input Current (L → H)	I <sub>FLH</sub>	I <sub>O</sub> = 0 mA, V <sub>O</sub> > 5 V		2.0	5.0	mA
	Threshold Input Voltage (H → L)	V <sub>FHL</sub>	I <sub>O</sub> = 0 mA, V <sub>O</sub> < 5 V	0.8			V

\*1 Typical values at T<sub>A</sub> = 25°C.

\*2 Maximum pulse width = 50 μs, Maximum duty cycle = 0.5%.

\*3 Maximum pulse width = 10 μs, Maximum duty cycle = 0.2%

\*4 V<sub>OH</sub> is measured with the DC load current in this testing (Maximum pulse width = 2 ms, Maximum duty cycle = 20%).

## SWITCHING CHARACTERISTICS

(V<sub>EE</sub> = GND, unless otherwise specified and refer to RECOMMENDED OPERATING CONDITIONS)

Parameter	Symbol	Conditions	MIN.	TYP.*1	MAX.	Unit	
Propagation Delay Time (L → H)	t <sub>PLH</sub>	R <sub>g</sub> = 10 Ω, C <sub>g</sub> = 10 nF, f = 10 kHz, Duty Cycle = 50%*2, I <sub>F</sub> = 10 mA		0.18	0.25	μs	
Propagation Delay Time (H → L)	t <sub>PHL</sub>			0.18	0.25	μs	
Pulse Width Distortion (PWD)	t <sub>PHL</sub> - t <sub>PLH</sub>				0.02	0.1	μs
Propagation Delay Time (Difference Between Any Two Products)	t <sub>PHL</sub> - t <sub>PLH</sub>			-0.1		0.1	μs
Rise Time	t <sub>r</sub>				50		ns
Fall Time	t <sub>f</sub>				50		ns
UVLO (Turn On Delay)	t <sub>UVLO ON</sub>	V <sub>O</sub> > 5 V, I <sub>F</sub> = 10 mA		0.8		μs	
UVLO (Turn Off Delay)	t <sub>UVLO OFF</sub>	V <sub>O</sub> < 5 V, I <sub>F</sub> = 10 mA		0.6		μs	
Common Mode Transient Immunity at High Level Output	CM <sub>H</sub>	T <sub>A</sub> = 25°C, I <sub>F</sub> = 10 mA, V <sub>CC</sub> = 30 V, V <sub>O (MIN.)</sub> = 26 V, V <sub>CM</sub> = 1.5 kV	25			kV/μs	
Common Mode Transient Immunity at Low Level Output	CM <sub>L</sub>	T <sub>A</sub> = 25°C, I <sub>F</sub> = 0 mA, V <sub>CC</sub> = 30 V, V <sub>O (MAX.)</sub> = 1 V, V <sub>CM</sub> = 1.5 kV	25			kV/μs	

\*1 Typical values at T<sub>A</sub> = 25°C.

\*2 This load condition is equivalent to the IGBT load at 1 200 V/75 A.

<R> TEST CIRCUIT

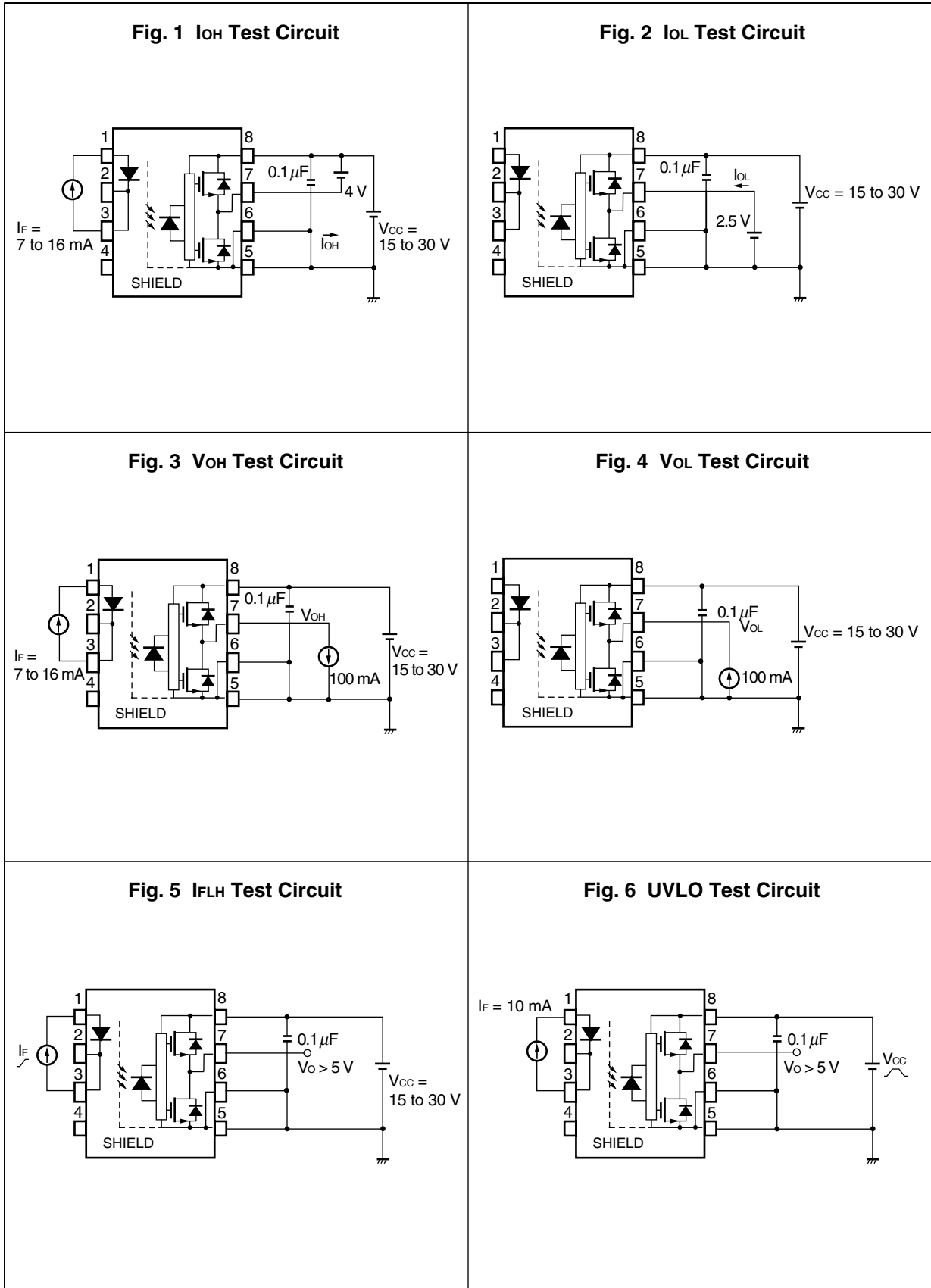




Fig. 7 t<sub>PLH</sub>, t<sub>PHL</sub>, t<sub>r</sub>, t<sub>f</sub> Test Circuit and Wave Forms

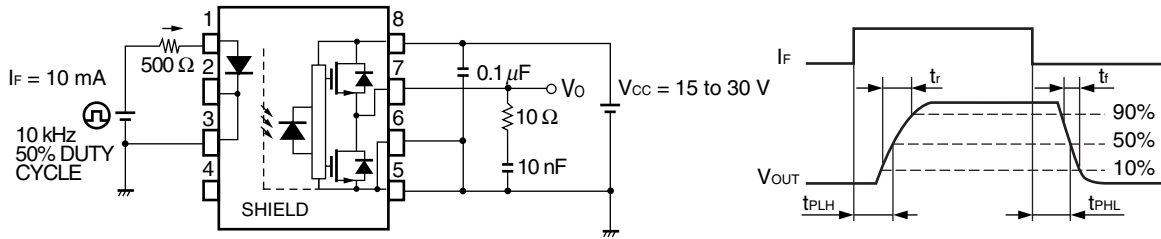
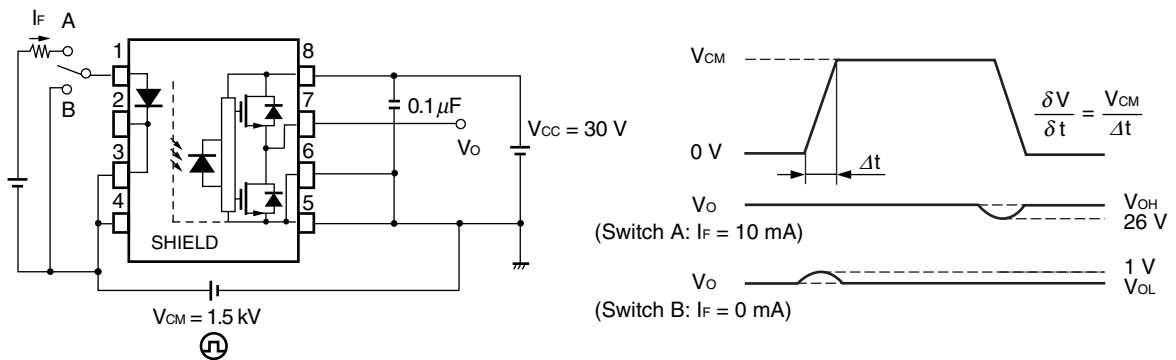
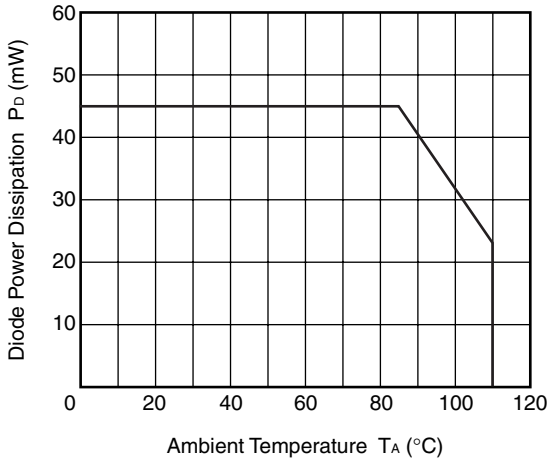


Fig. 8 CMR Test Circuit and Wave Forms

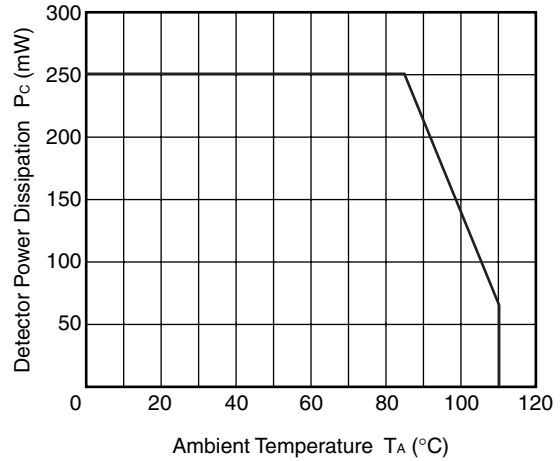


<R> TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise specified)

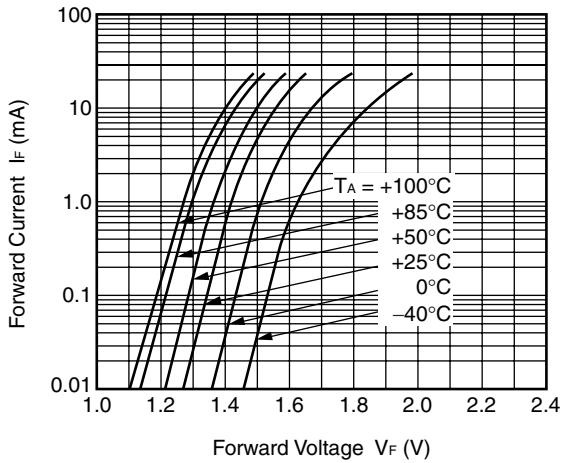
DIODE POWER DISSIPATION vs. AMBIENT TEMPERATURE



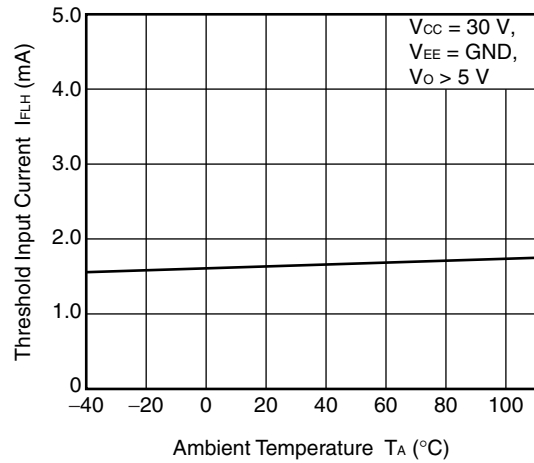
DETECTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE



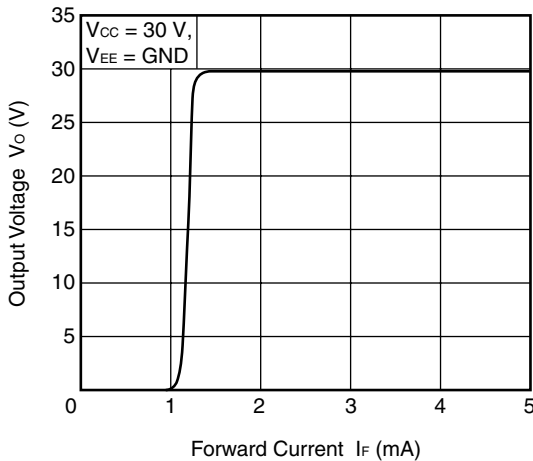
FORWARD CURRENT vs. FORWARD VOLTAGE



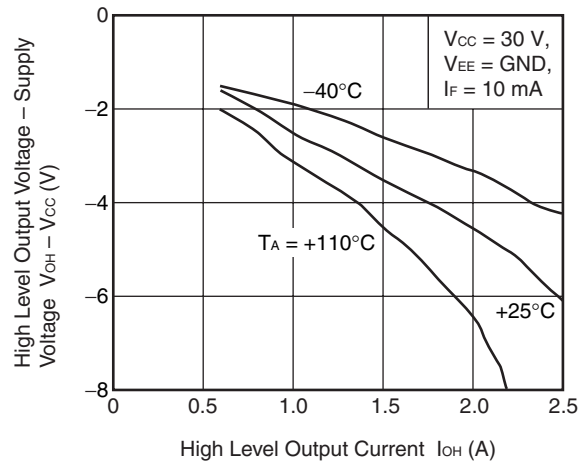
THRESHOLD INPUT CURRENT vs. AMBIENT TEMPERATURE



OUTPUT VOLTAGE vs. FORWARD CURRENT

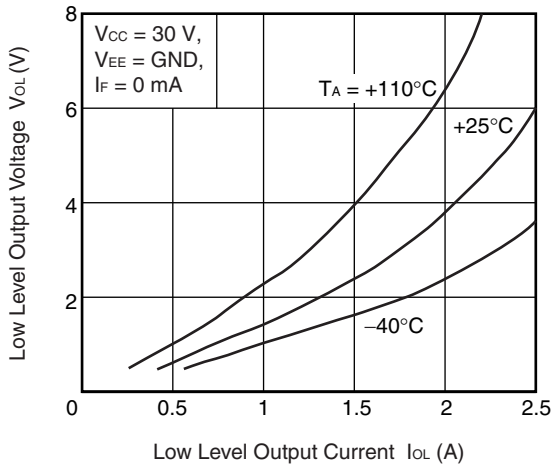


HIGH LEVEL OUTPUT VOLTAGE – SUPPLY VOLTAGE vs. HIGH LEVEL OUTPUT CURRENT

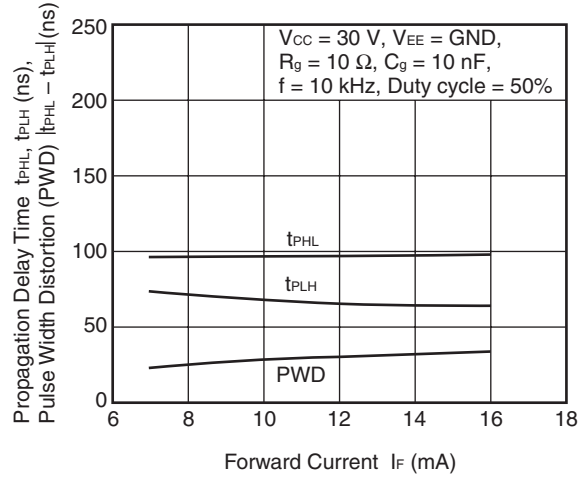


**Remark** The graphs indicate nominal characteristics.

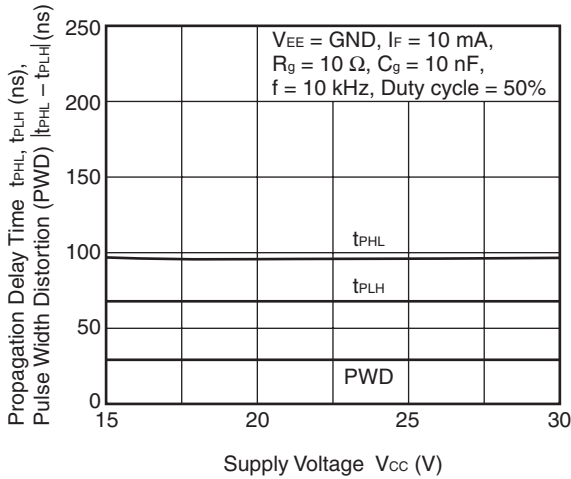
LOW LEVEL OUTPUT VOLTAGE vs. LOW LEVEL OUTPUT CURRENT



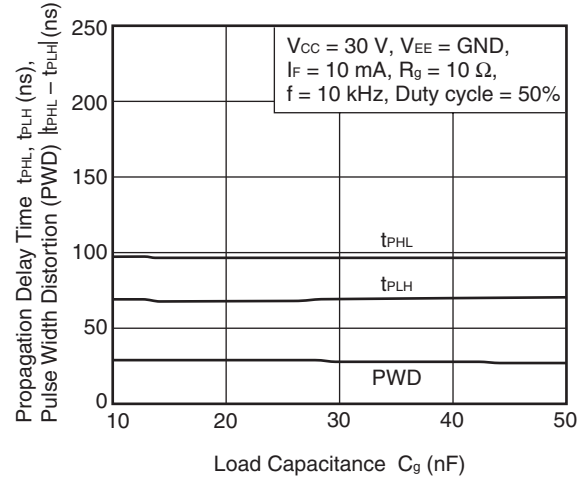
PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. FORWARD CURRENT



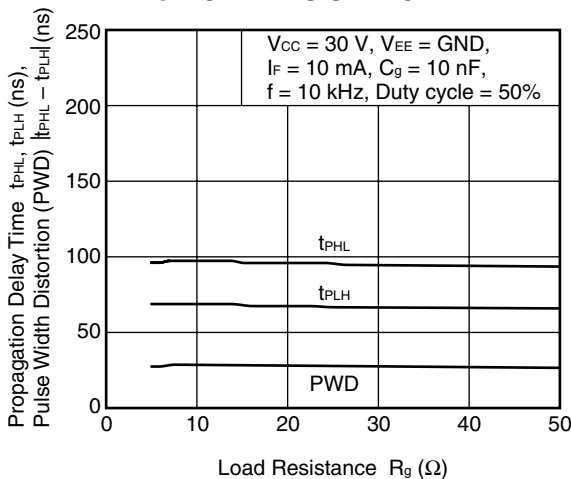
PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. SUPPLY VOLTAGE



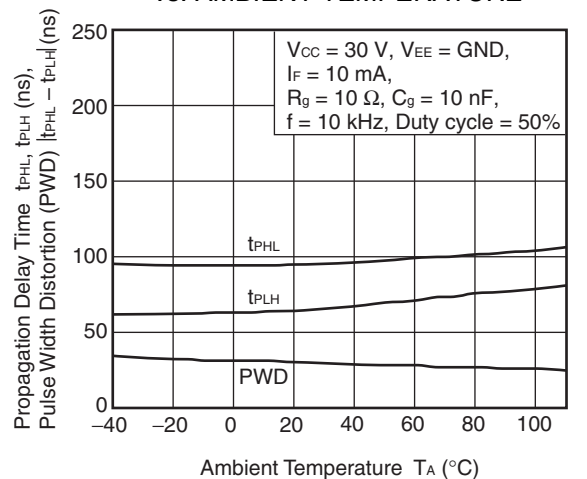
PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. LOAD CAPACITANCE



PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. LOAD RESISTANCE

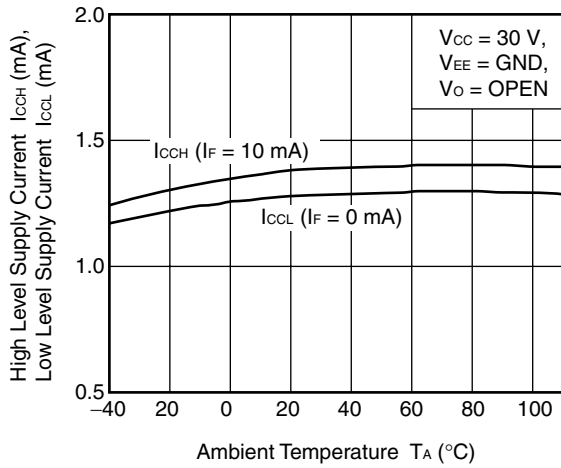


PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. AMBIENT TEMPERATURE

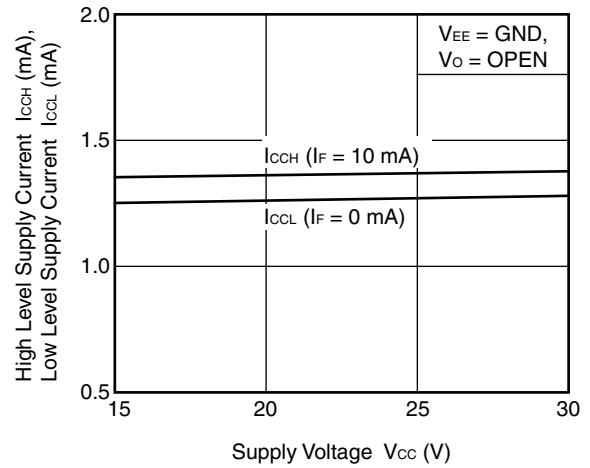


**Remark** The graphs indicate nominal characteristics.

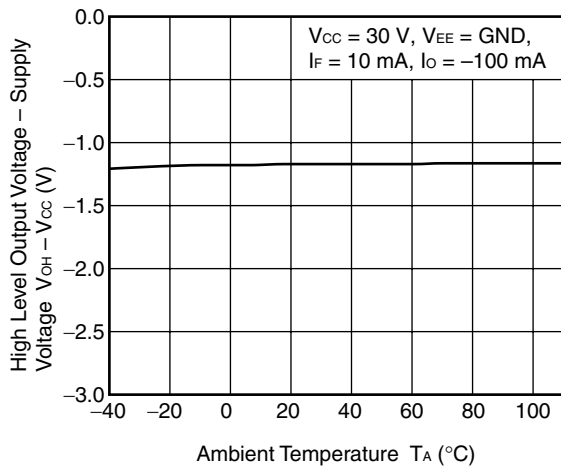
SUPPLY CURRENT vs. AMBIENT TEMPERATURE



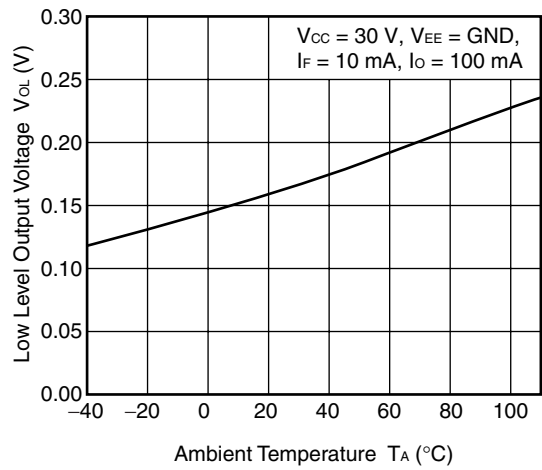
SUPPLY CURRENT vs. SUPPLY VOLTAGE



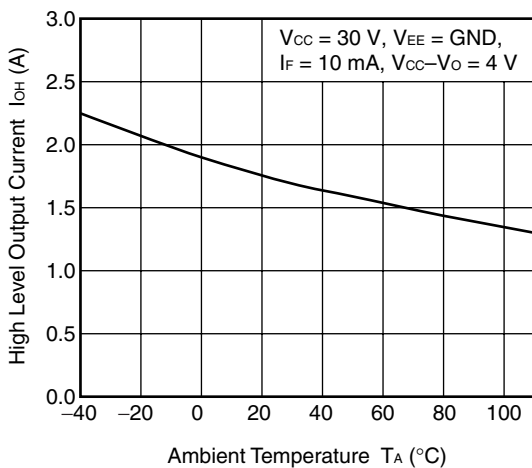
HIGH LEVEL OUTPUT VOLTAGE – SUPPLY VOLTAGE vs. AMBIENT TEMPERATURE



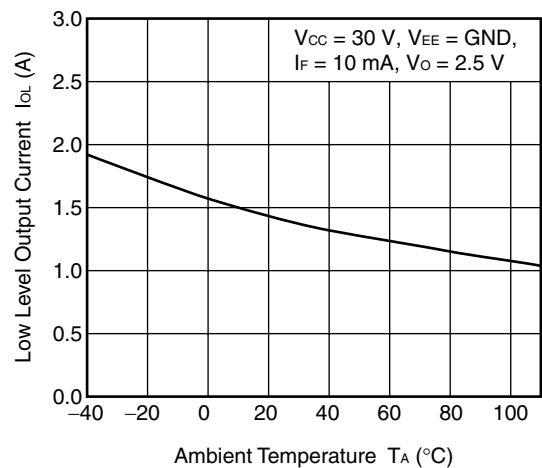
LOW LEVEL OUTPUT VOLTAGE vs. AMBIENT TEMPERATURE



HIGH LEVEL OUTPUT CURRENT vs. AMBIENT TEMPERATURE

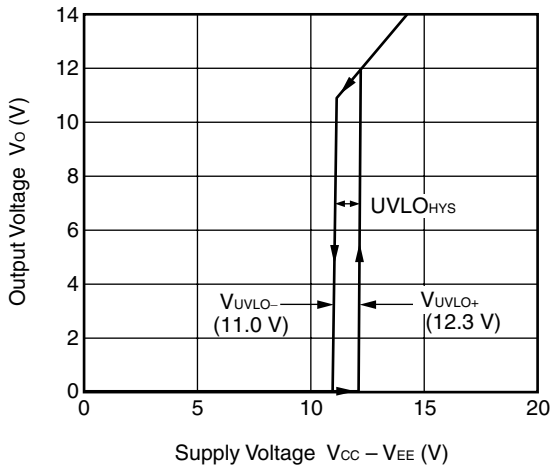


LOW LEVEL OUTPUT CURRENT vs. AMBIENT TEMPERATURE



**Remark** The graphs indicate nominal characteristics.

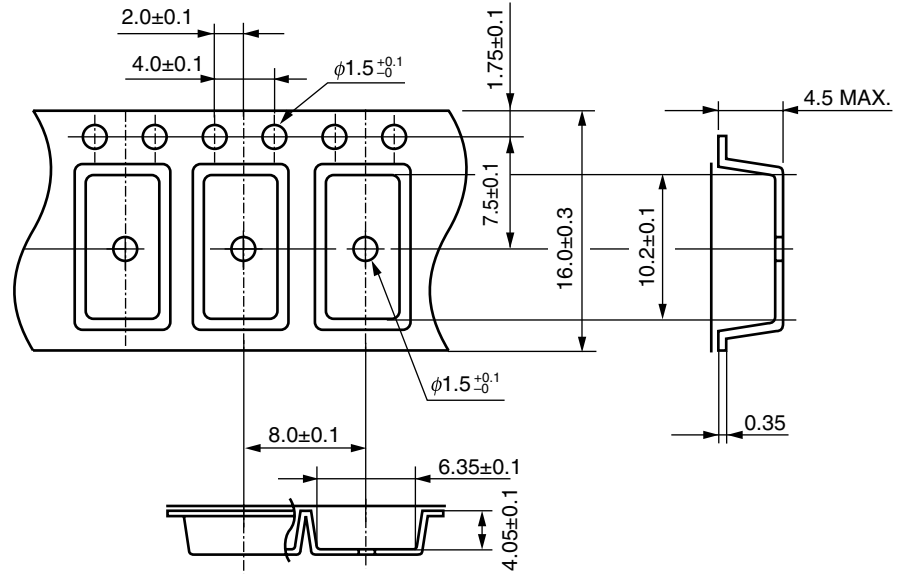
OUTPUT VOLTAGE vs. SUPPLY VOLTAGE



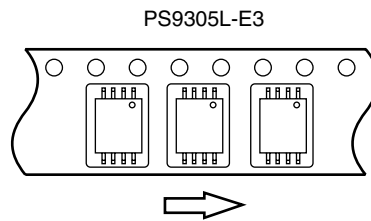
**Remark** The graph indicates nominal characteristics.

<R> TAPING SPECIFICATIONS (UNIT: mm)

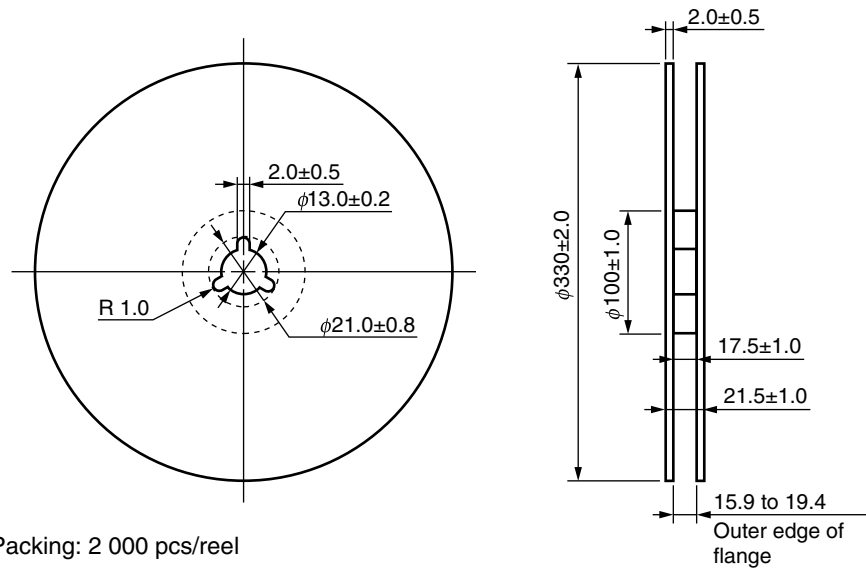
Outline and Dimensions (Tape)



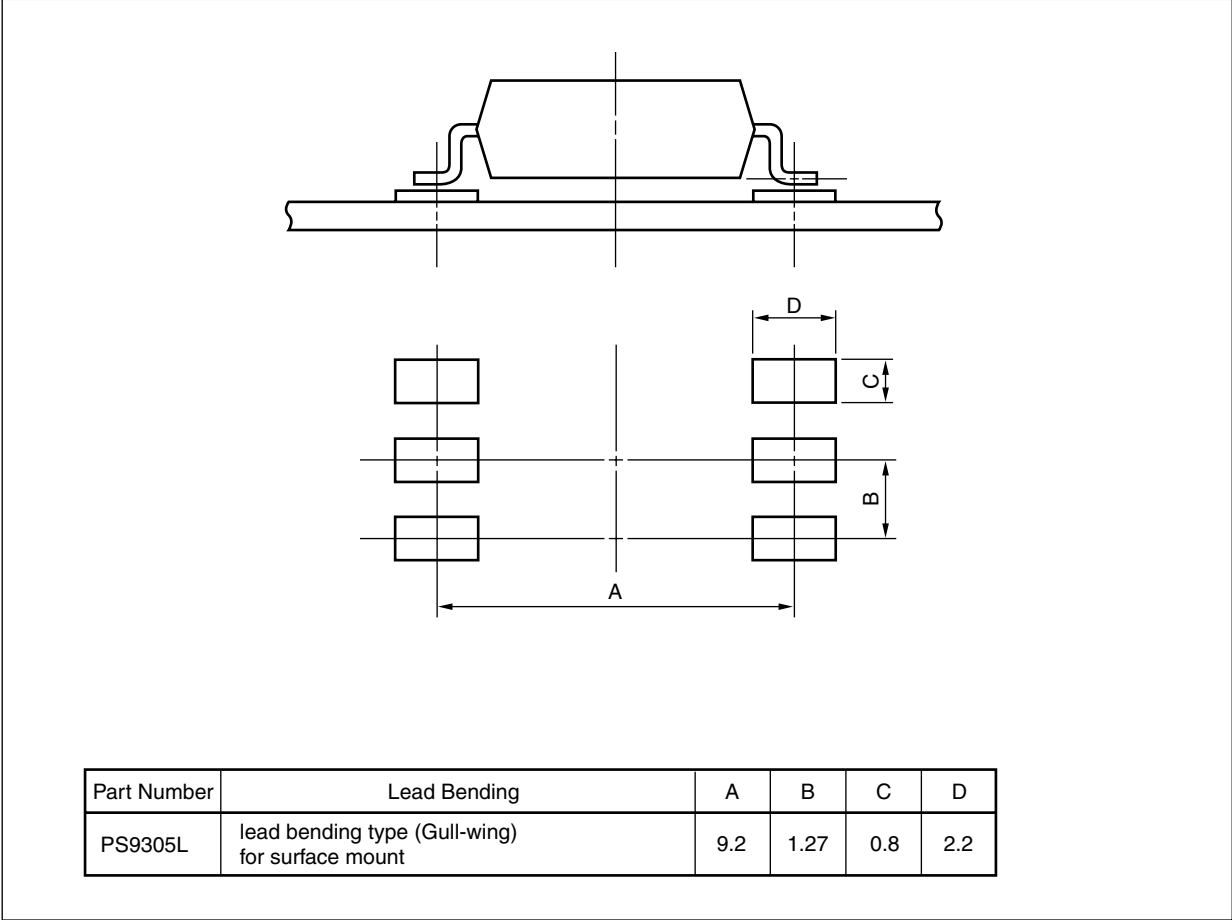
Tape Direction



Outline and Dimensions (Reel)



<R> RECOMMENDED MOUNT PAD DIMENSIONS (UNIT: mm)

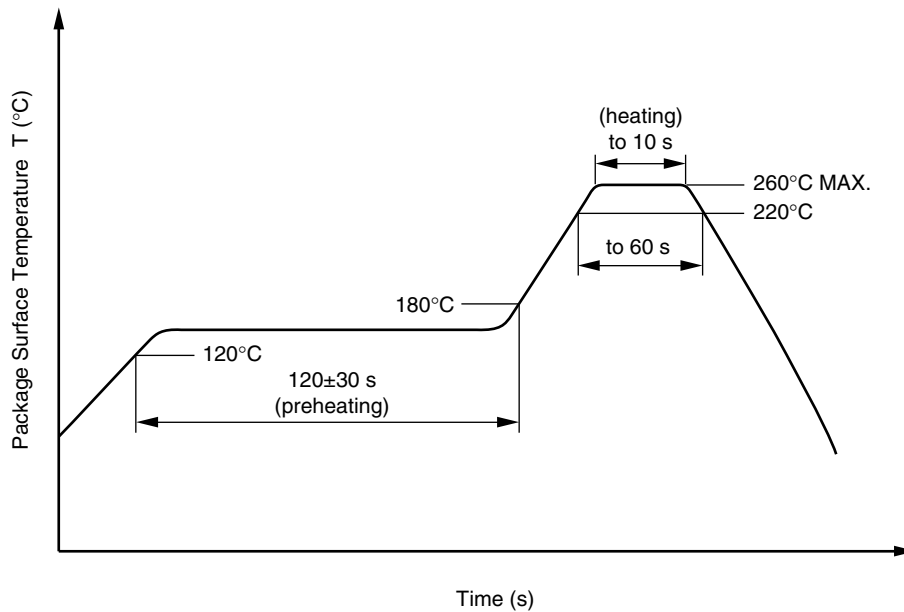


## &lt;R&gt; NOTES ON HANDLING

**1. Recommended soldering conditions****(1) Infrared reflow soldering**

- Peak reflow temperature 260°C or below (package surface temperature)
- Time of peak reflow temperature 10 seconds or less
- Time of temperature higher than 220°C 60 seconds or less
- Time to preheat temperature from 120 to 180°C 120±30 s
- Number of reflows Three
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

Recommended Temperature Profile of Infrared Reflow

**(2) Wave soldering**

- Temperature 260°C or below (molten solder temperature)
- Time 10 seconds or less
- Preheating conditions 120°C or below (package surface temperature)
- Number of times One (Allowed to be dipped in solder including plastic mold portion.)
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

**(3) Soldering by Soldering Iron**

- Peak Temperature (lead part temperature) 350°C or below
- Time (each pins) 3 seconds or less
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

(a) Soldering of leads should be made at the point 1.5 to 2.0 mm from the root of the lead



**(4) Cautions**

- Fluxes

Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

**2. Cautions regarding noise**

Be aware that when voltage is applied suddenly between the photocoupler's input and output at startup, the output transistor may enter the on state, even if the voltage is within the absolute maximum ratings.

**USAGE CAUTIONS**

1. This product is weak for static electricity by designed with high-speed integrated circuit so protect against static electricity when handling.
2. Board designing
  - (1) By-pass capacitor of more than 0.1  $\mu$ F is used between Vcc and GND near device. Also, ensure that the distance between the leads of the photocoupler and capacitor is no more than 10 mm.
  - (2) In order to avoid malfunctions and characteristics degradation, IGBT collector or emitter traces should not be closed to the LED input.
  - (3) Pin 4 (which is an NC<sup>\*1</sup> pin) can either be connected directly to the GND pin on the LED side or left open.  
Unconnected pins should not be used as a bypass for signals or for any other similar purpose because this may degrade the internal noise environment of the device.  
**\*1 NC: Non-Connection (No Connection)**
3. Make sure the rise/fall time of the forward current is 0.5  $\mu$ s or less.
4. In order to avoid malfunctions, make sure the rise/fall slope of the supply voltage is 3 V/ $\mu$ s or less.
5. Avoid storage at a high temperature and high humidity.

## SPECIFICATION OF VDE MARKS LICENSE DOCUMENT

Parameter	Symbol	Spec.	Unit
Climatic test class (IEC 60068-1/DIN EN 60068-1)		40/110/21	
Dielectric strength maximum operating isolation voltage	$U_{IORM}$	1 130	$V_{peak}$
Test voltage (partial discharge test, procedure a for type test and random test) $U_{pr} = 1.5 \times U_{IORM}$ , $P_d < 5$ pC	$U_{pr}$	1 695	$V_{peak}$
Test voltage (partial discharge test, procedure b for all devices) $U_{pr} = 1.875 \times U_{IORM}$ , $P_d < 5$ pC	$U_{pr}$	2 119	$V_{peak}$
Highest permissible overvoltage	$U_{TR}$	8 000	$V_{peak}$
Degree of pollution (DIN EN 60664-1 VDE0110 Part 1)		2	
Comparative tracking index (IEC 60112/DIN EN 60112 (VDE 0303 Part 11))	CTI	175	
Material group (DIN EN 60664-1 VDE0110 Part 1)		III a	
Storage temperature range	$T_{stg}$	-55 to +125	°C
Operating temperature range	$T_A$	-40 to +110	°C
Isolation resistance, minimum value $V_{IO} = 500$ V dc at $T_A = 25^\circ\text{C}$ $V_{IO} = 500$ V dc at $T_A$ MAX. at least $100^\circ\text{C}$	Ris MIN. Ris MIN.	$10^{12}$ $10^{11}$	$\Omega$ $\Omega$
Safety maximum ratings (maximum permissible in case of fault, see thermal derating curve)			
Package temperature	$T_{si}$	175	°C
Current (input current $I_F$ , $P_{si} = 0$ )	$I_{si}$	400	mA
Power (output or total power dissipation)	$P_{si}$	700	mW
Isolation resistance $V_{IO} = 500$ V dc at $T_A = T_{si}$	Ris MIN.	$10^9$	$\Omega$

<b>Caution</b> GaAs Products	<p>This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.</p> <ul style="list-style-type: none"><li>• Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.<ol style="list-style-type: none"><li>1. Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.</li><li>2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.</li></ol></li><li>• Do not burn, destroy, cut, crush, or chemically dissolve the product.</li><li>• Do not lick the product or in any way allow it to enter the mouth.</li></ul>
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## Revision History

## PS9305L Data Sheet

Rev.	Date	Description	
		Page	Summary
0.01	May 12, 2010	–	First Edition issued
1.00	May 16, 2011	Throughout	Preliminary Data Sheet -> Data Sheet
		Throughout	Safety standards approved
		p.3	Modification of <b>MARKING EXAMPLE</b>
		p.4	Addition of <b>ORDERING INFORMATION</b>
		p.4	Modification of <b>ABSOLUTE MAXIMUM RATINGS</b>
		p.5	Modification of <b>ELECTRICAL CHARACTERISTICS</b> $I_{CCH}$ , $I_{CCL}$
		p.6	Modification of <b>SWITCHING CHARACTERISTICS</b> $ t_{PHL}-t_{PLH} $
		pp.7, 8	Addition of <b>TEST CIRCUIT</b>
		pp.9 to 12	Addition of <b>TYPICAL CHARACTERISTICS</b>
		p.13	Addition of <b>TAPING SPECIFICATIONS</b>
		p.14	Addition of <b>RECOMMENDED MOUNT PAD DIMENSIONS</b>
		pp.15, 16	Addition of <b>NOTES ON HANDLING</b>
		p.17	Addition of <b>SPECIFICATION OF VDE MARKS LICENSE DOCUMENT</b>

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